

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device,  
including forming a gate electrode or dummy gate on a  
fin-type silicon layer, introducing an impurity into  
5 the fin-type silicon layer with the gate electrode or  
dummy gate used as mask so as to form first impurity  
regions, etching the gate electrode or dummy gate so as  
to form a gate electrode or dummy gate having a reduced  
size, and introducing an impurity into the fin-type  
10 silicon layer with the gate electrode or dummy gate of  
the reduced size used as a mask so as to form second  
impurity regions positioned adjacent to the first  
impurity diffusion regions.